

CHAPTER ONE

*Properties of Digital
Integrated Ccts.*

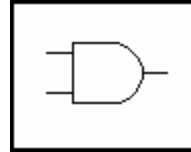
Digital Electronics.

Basic Logic Operations

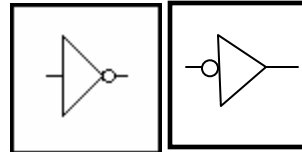
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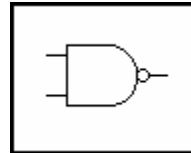
• AND



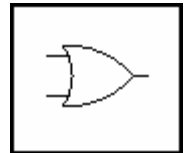
• NOT



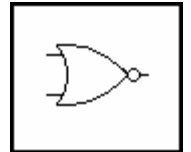
• NAND



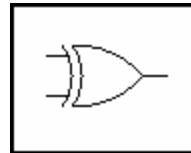
• OR



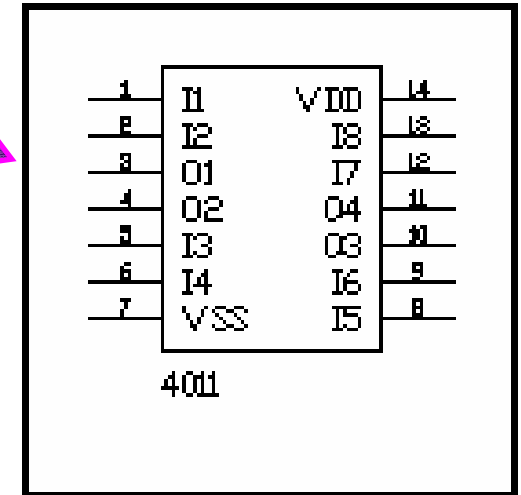
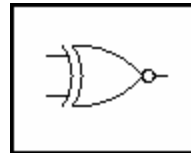
• NOR



• XOR



• XNOR



4 2-in AND

4 inputs with
two AND gates

Basic Logic Operations

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- Combinational logic:
Output depends only on present value of the input.
- Sequential logic:
Output depends on present/past value of the input.

Basic Logic Operations

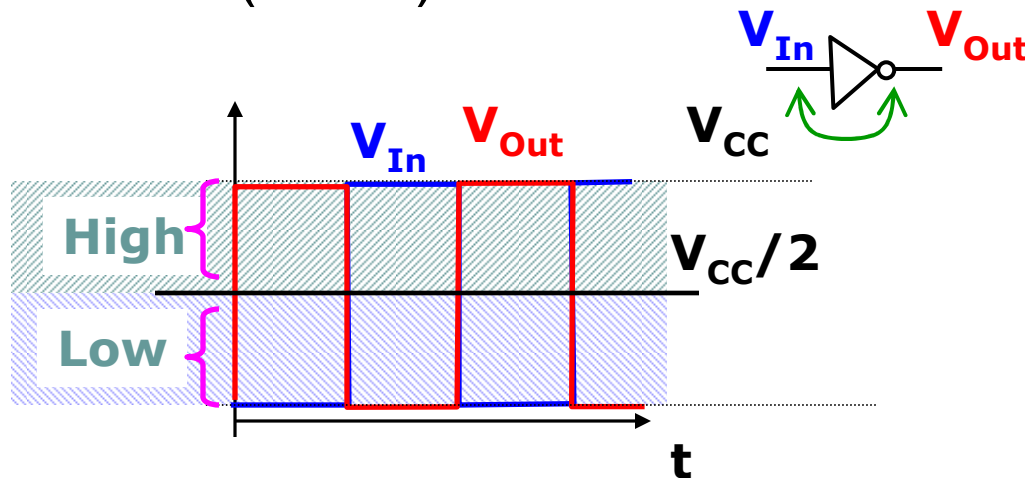
- The voltages/currents in digital logic circuits have two possible states (*according to positive voltage logic*)✓:
 - Low voltage corresponds to a binary 0
 - High voltage corresponds to a binary 1
- *But according to negative voltage logic:*
 - Low voltage corresponds to a binary 1
 - High voltage corresponds to a binary 0

Basic Building Blocks

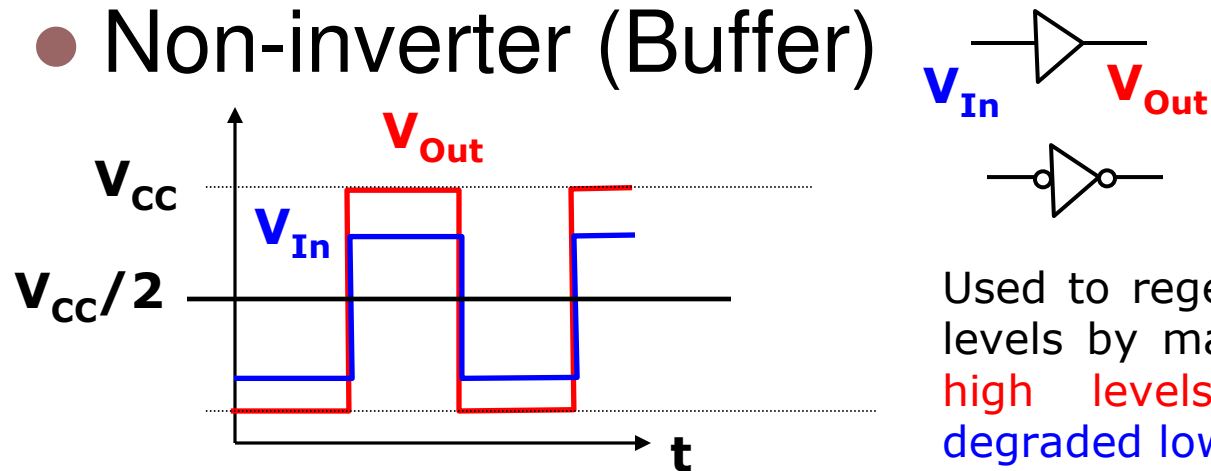
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- Inverter (NOT)



- Non-inverter (Buffer)

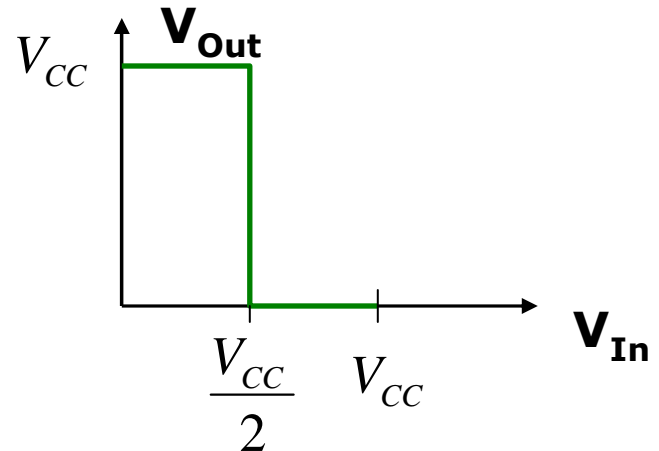


Used to regenerate voltage levels by making degraded high levels higher and degraded low levels lower

Voltage Transfer Characteristics (VTC) of Inverters

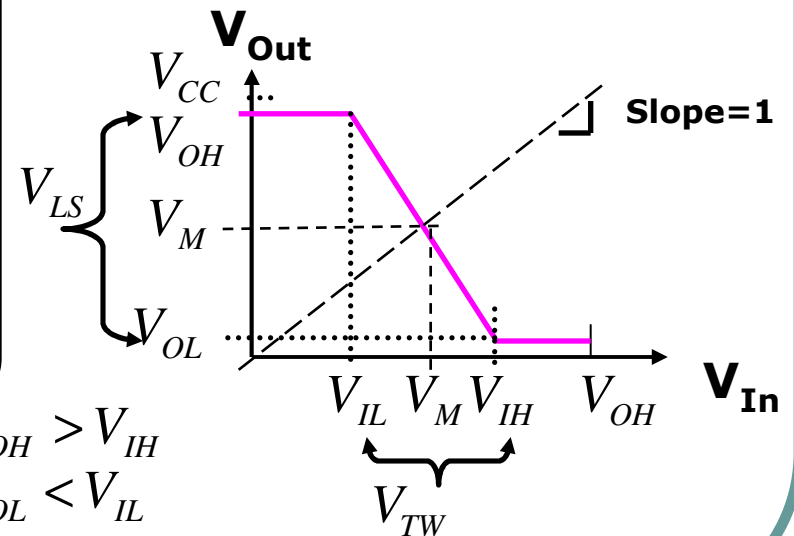
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● Ideal



● Practical

1. V_{OH} : Output high voltage level
2. V_{OL} : Output low voltage level
3. V_{IL} : Max. Input voltage that provides high output voltage
4. V_{IH} : Min. Input voltage that provides low output voltage
5. V_M : Midpoint ($V_{Out} = V_{In}$) ideally $\sim V_{CC}/2$
6. V_{LS} : Logic swing voltage. change in input to cause a change in output
5. V_{TW} : Transition width

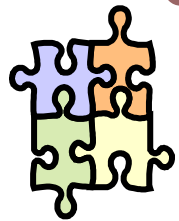


The outputs of present inverter will be inputs to the next gate, "Low and High levels must be distinguishable"

Voltage Transfer Characteristics (VTC) of Inverters

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Example

Assume $V_{OH} = 4.3 \text{ V}$, $V_{OL} = 0.2 \text{ V}$, $V_{IL} = 0.7 \text{ V}$, $V_{IH} = 0.9 \text{ V}$

Calculate V_{LS} , V_{TW} and V_M

Solution

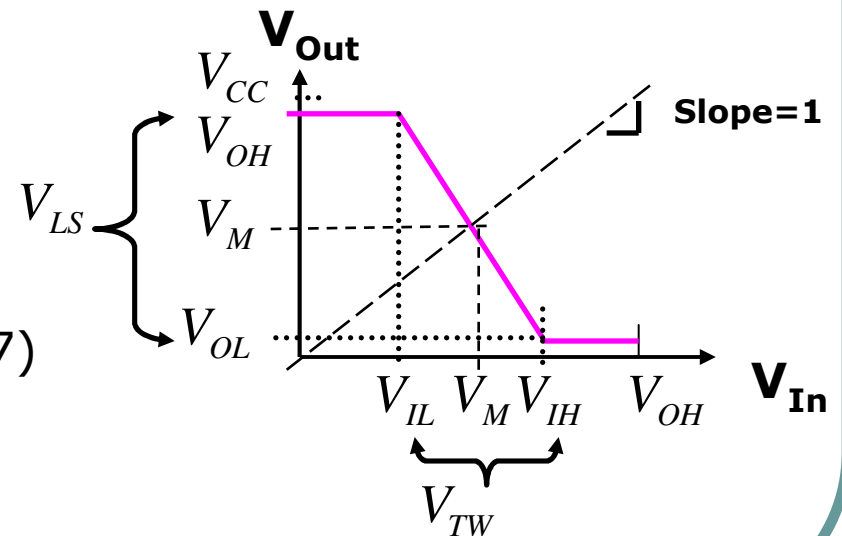
$$V_{LS} = 4.1 \text{ V},$$
$$V_{TW} = 0.2 \text{ V},$$

$$Y - y_0 = \text{slope}(x - x_0)$$

$$Y - 4.3 = [(0.2 - 4.3) / (0.9 - 0.7)](x - 0.7)$$

$$Y = x \rightarrow y = 0.867 \text{ V}$$

$$\rightarrow V_M = 0.867 \text{ V} \quad \text{far from } V_{CC}/2$$



Noise in Digital Ccts.

- **Noise:** Fluctuations (variations, degradations) of the steady state voltage levels
- **Noise margins:**
 - Low noise margin
 - High noise margin
- **Noise Sensitivities:**
 - Low noise sensitivity
 - High noise sensitivity
- **Noise Immunities** (ability of a gate to reject noise)
 - Low noise immunity

$$V_{NML} = V_{IL} - V_{OL}$$

$$V_{NMH} = V_{OH} - V_{IH}$$

Safety margins
(have to be positive)

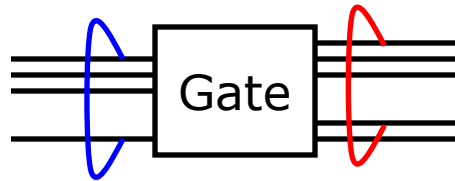
$$V_{NSL} = V_M - V_{OL}$$

$$V_{NSH} = V_{OH} - V_M$$

$$V_{NIL} = V_{OL} / V_{LS}$$

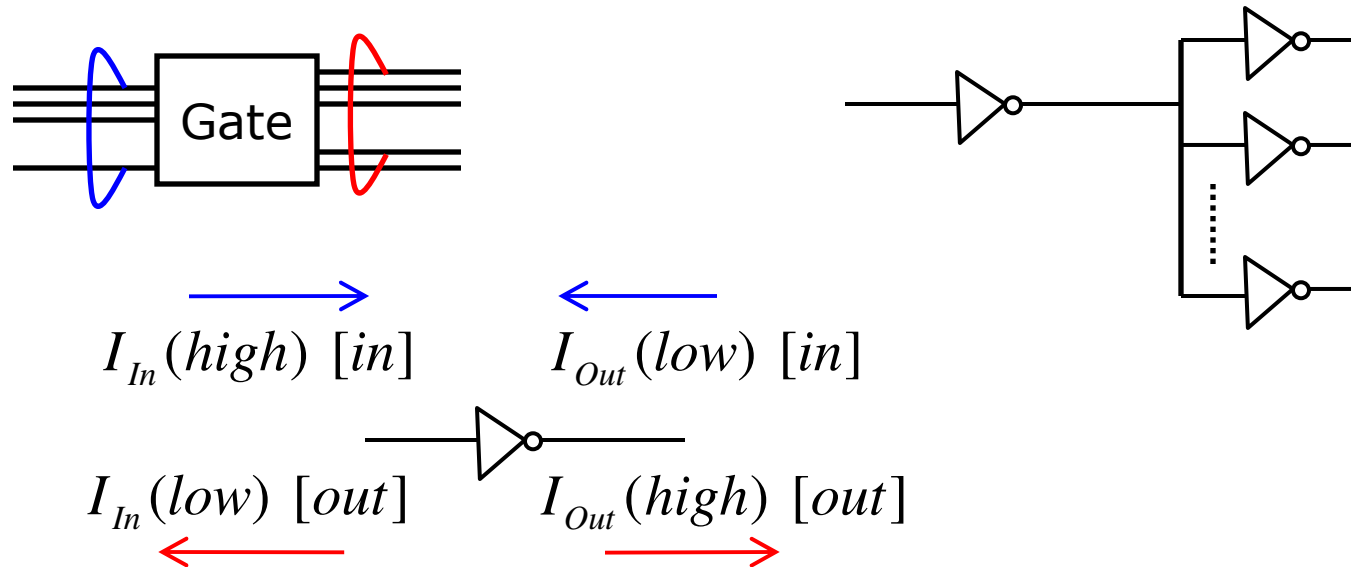
$$V_{NIH} = V_{NSH} / V_{LS}$$

Fan-In and Fan-Out



- Fan-In: (less concern)
Number of inputs of a gate.
- Fan-Out:
Number of outputs of a gate.

Maximum Fan-Out of a Digital Gate

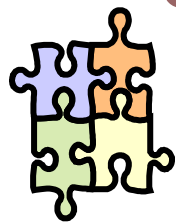


- Maximum Fan-out = $\min\{N_{low}, N_{high}\}$

$$N_{low} = \frac{I_{Out}(low)}{I_{In}(low)}$$

$$N_{high} = \frac{I_{Out}(high)}{I_{In}(high)}$$

Maximum Fan-Out of a Digital Gate



Example

Assume $I_{In}(high) = 98.9\mu A$ $I_{In}(low) = 2.43mA$
 $I_{Out}(high) = 71.4mA$ $I_{Out}(low) = 54.3mA$

Calculate the **maximum fan-out**.

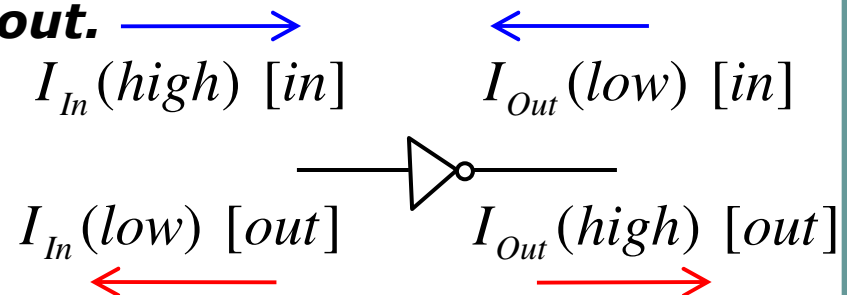
Solution

$$N_{low} = \frac{I_{Out}(low)}{I_{In}(low)} = \frac{54.3}{2.43} = 22.3$$

$$N_{high} = \frac{I_{Out}(high)}{I_{In}(high)} = \frac{71.4}{0.0989} = 721.9$$



maximum fan-out = 22



Rounded to the
nearest lowest integer

Transient Characteristics

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- Switching speed

Associated with charging and discharging the load capacitances

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t_d = delay time

t_r = rise time

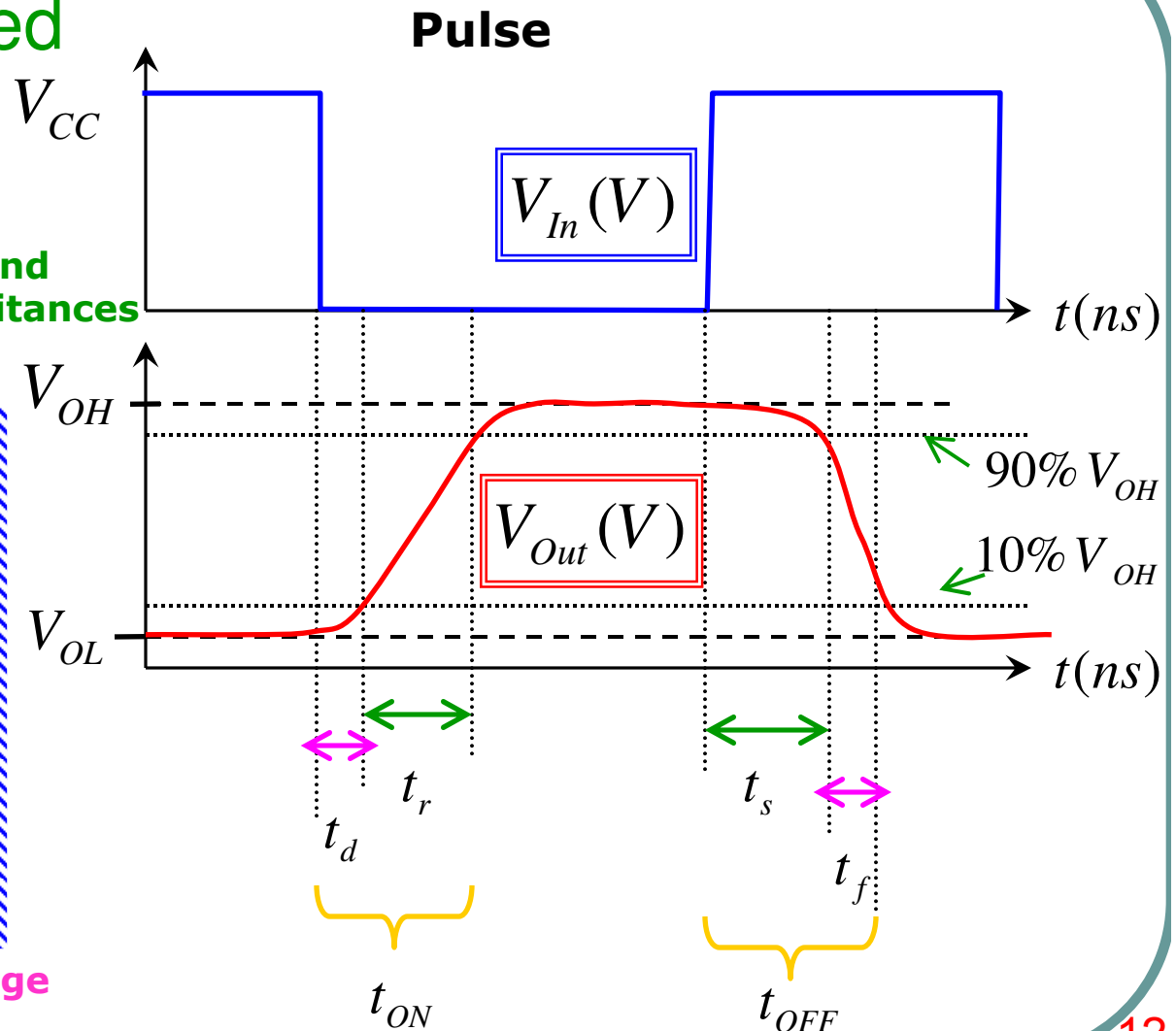
t_s = storage time

t_f = fall time

t_{ON} = turn - on time = $t_d + t_r$

t_{OFF} = turn - off time = $t_s + t_f$

Associated with stored charge of pn junction



Transient Characteristics

- Switching voltage high \Leftrightarrow low requires a finite amount of time, i.e., the output does not respond immediately (delay).
- *Propagation delay time (PDT)*: is the time interval between the application of an input and the response of the resulting output.
- In **BJTs**, PDT is caused by the time required to store and remove the charge from the **base region**.
- In **MOSFETs**, PDT is caused by the **metal oxide capacitance**

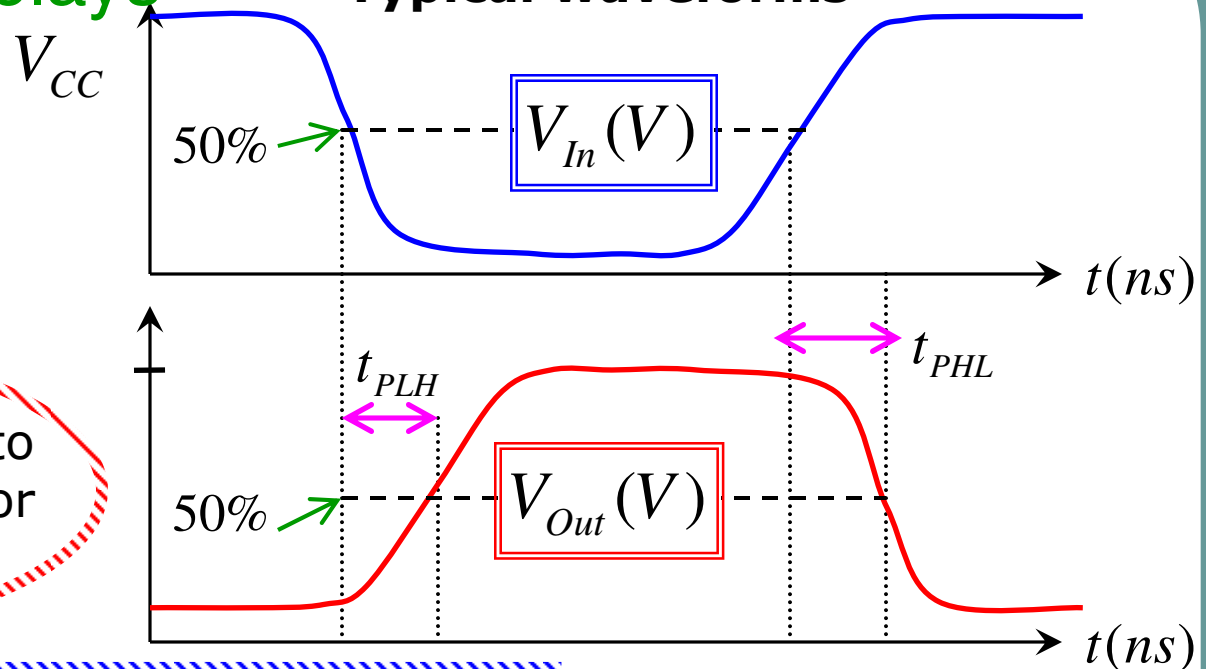
Transient Characteristics

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- Propagation delays

Typical waveforms



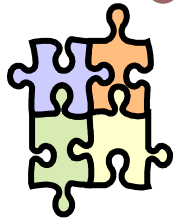
The 50% points are used to define the time required for the output to respond

t_{PLH} = refers to low - to - high transition of the output

t_{PHL} = refers to high - to - low transition of the output

$$t_p(avg) = \frac{t_{PLH} + t_{PHL}}{2}$$

Transient Characteristics



Example

See example **1.5** on page 9

Transient Characteristics

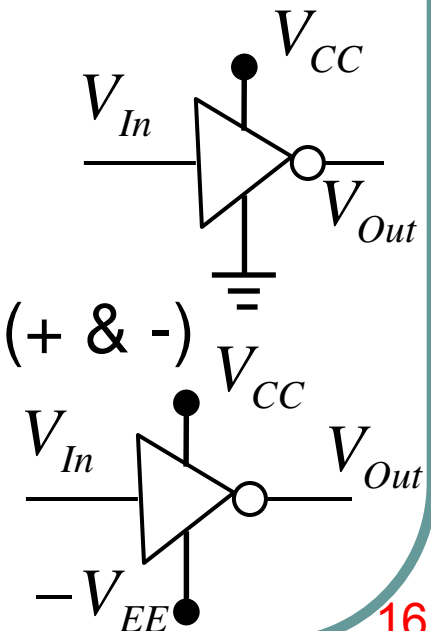
- Power dissipation:

- An ideal gate has a single power supply
- The power dissipated equals the power supplied
- The dissipated power in logic high and logic low states may differ

$$P_{CC}(avg) = \frac{P_{CC}(OH) + P_{CC}(OL)}{2}$$
$$= \left(\frac{I_{CC}(OH) + I_{CC}(OL)}{2} \right) V_{CC}$$

- Some gates have two power supplies (+ & -)

$$P_{DISS}(avg) = P_{CC}(avg) + P_{EE}(avg)$$
$$= \left(\frac{I_{CC}(OH) + I_{CC}(OL)}{2} \right) V_{CC} + \left(\frac{I_{EE}(OH) + I_{EE}(OL)}{2} \right) V_{EE}$$



Transient Characteristics

- **Power-Delay product (*speed-power product*):**
 - Low power dissipation and short propagation delay are desirable for digital ICs.
 - But, faster propagation delay times are achieved at the cost of increased power dissipation.
 - As a figure of merit, power-delay product is defined as
$$PD = P_{DISS}(avg) \times t_p(avg) \quad [J]: \text{joules}$$
 - The smaller the PD is, the more ideal the gate is.
Ideally PD=0 J.

Assignment # 1

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- HW #1: Solve Problems: 1.1, 1.5, 1.12, 1.22, and 1.24